

### REMARKS

Claims 1, 4 and 6 have been amended and claims 12 to 14 have been added.

Claims 1 to 14 are not active in this application.

Claims 1 to 11 were rejected under 35 U.S.C. 102(b) as being anticipated by Blewer et al. (U.S. 5,023,200). The rejection is respectfully traversed.

Each of claims 1, 4 and 6 require the step of sealing the surface. No such step is taught or suggested by Blewer et al. either alone or in the total combination as claimed.

Each of claims 1, 4 and 6 further requires the step of implanting an oxidizing species through the epitaxial layer into the porous semiconductor material. No such step is taught or suggested by Blewer et al. either alone or in the total combination as claimed.

Claims 2, 3 and 9 depend from claim 1, claims 5 and 10 depends from claim 4 and claims 7, 8 and 11 depend from claim 6 and therefore define patentably over Blewer et al. for at least the reasons presented above with reference to the claims from which these claims depend.

In addition, claim 2 further limits claim 1 by requiring that the oxidizing species consist essentially of oxygen. No such step is taught or suggested by Blewer et al. either alone or in the total combination as claimed.

Claim 3 further limits claim 1 by requiring that the semiconductor layer consist essentially of silicon. No such step is taught or suggested by Blewer et al. in the total combination as claimed.

Claim 5 further limits claim 4 by requiring that the semiconductor layer consist essentially of silicon. No such step is taught or suggested by Blewer et al. in the total combination as claimed.

Claim 7 further limits claim 6 by requiring that the oxidizing species consist essentially of oxygen. No such step is taught or suggested by Blewer et al. either alone or in the total combination as claimed.

Claim 8 further limits claim 6 by requiring that the semiconductor layer consist essentially of silicon. No such step is taught or suggested by Blewer et al. in the total combination as claimed.

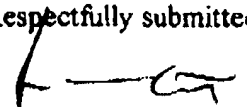
Claim 12 further limits claim 1 by requiring that the step of sealing include heating said porous semiconductor material in a hydrogen ambient.

Claim 13 further limit claim 4 by requiring that the step of sealing include heating said porous semiconductor material in a hydrogen ambient. No such step is taught or suggested by Blewer et al. either alone or in the total combination as claimed.

Claim 14 further limit claim 6 by requiring that the step of sealing include heating said porous semiconductor material in a hydrogen ambient. No such step is taught or suggested by Blewer et al. either alone or in the total combination as claimed.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,



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